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NTE ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE2365
Silicon NPN Transistor
High Voltage Horizontal Deflection Output

Features:
- High Speed: t_f = 100ns typ
- High Reliability
- High Breakdown Voltage: V_{CBO} = 1500V

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector to Base Voltage, V_{CBO} 1500V
Collector to Emitter Voltage, V_{CEO} 800V
Emitter to Base Voltage, V_{EBO} 6V
Collector Current, I_C
  Continuous 12A
  Peak 30A
Collector Dissipation, P_C 180W
Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 800V, I_E = 0	–	–	10	µA
	I_{CES}	V_{CE} = 1500V, R_{BE} = 0	–	–	1.0	mA
Collector Sustaining Voltage	$V_{CEO(sus)}$	I_C = 100mA, I_B = 0	800	–	–	V
Emitter Cutoff Current	I_{EBO}	V_{EB} = 4V, I_C = 0	–	–	1.0	mA
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 10A, I_B = 2.5A	–	–	5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 10A, I_B = 2.5A	–	–	1.5	V
DC Current Gain	$h_{FE(1)}$	V_{CE} = 5V, I_C = 1A	8	–	30	
	$h_{FE(2)}$	V_{CE} = 5V, I_C = 10A	4	–	8	
Storage Time	t_{stg}	I_C = 8A, I_{B1} = 1.6A, I_{B2} = –3.2A	–	–	3.0	µs
Fall Time	t_f		–	–	0.2	µs

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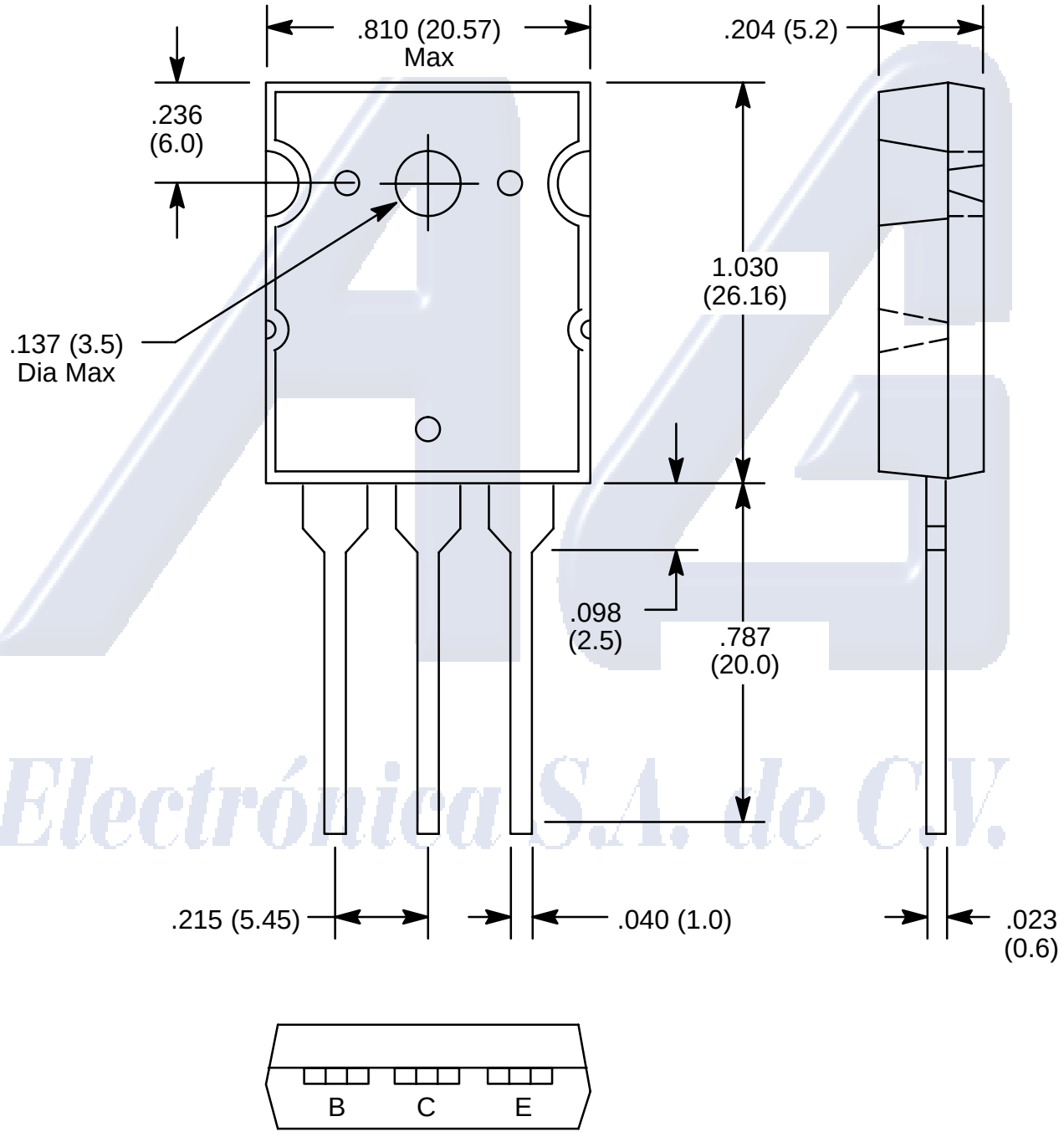

Note: **Pin2** connected to metal part of mounting surface.

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